

# Complementary Power Transistors

## DPAK for Surface Mount Applications

### MJD44H11 (NPN), MJD45H11 (PNP)

Designed for general purpose power and switching such as output or driver stages in applications such as switching regulators, converters, and power amplifiers.

#### Features

- Lead Formed for Surface Mount Application in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("–1" Suffix)
- Electrically Similar to Popular D44H/D45H Series
- Low Collector Emitter Saturation Voltage
- Fast Switching Speeds
- Complementary Pairs Simplifies Designs
- Epoxy Meets UL 94 V–0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

**MAXIMUM RATINGS** ( $T_A = 25^\circ\text{C}$ , common for NPN and PNP, minus sign, "–", for PNP omitted, unless otherwise noted)

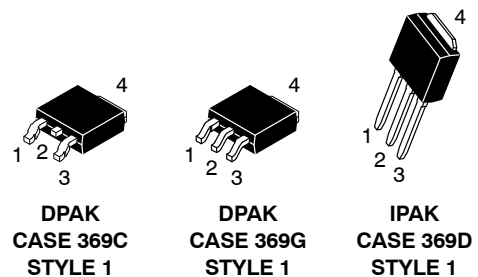
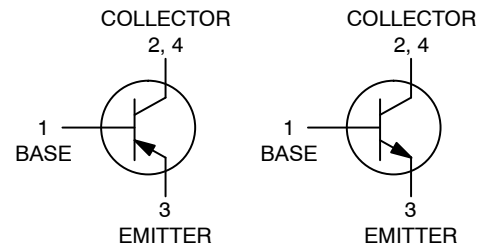
| Rating                                                                                            | Symbol         | Max           | Unit                     |
|---------------------------------------------------------------------------------------------------|----------------|---------------|--------------------------|
| Collector–Emitter Voltage                                                                         | $V_{CEO}$      | 80            | Vdc                      |
| Emitter–Base Voltage                                                                              | $V_{EB}$       | 5             | Vdc                      |
| Collector Current – Continuous                                                                    | $I_C$          | 8             | Adc                      |
| Collector Current – Peak                                                                          | $I_{CM}$       | 16            | Adc                      |
| Total Power Dissipation<br>@ $T_C = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$          | $P_D$          | 20<br>0.16    | W<br>W/ $^\circ\text{C}$ |
| Total Power Dissipation (Note 1)<br>@ $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$          | 1.75<br>0.014 | W<br>W/ $^\circ\text{C}$ |
| Operating and Storage Junction<br>Temperature Range                                               | $T_J, T_{stg}$ | –55 to +150   | $^\circ\text{C}$         |
| ESD – Human Body Model                                                                            | HBM            | 3B            | V                        |
| ESD – Machine Model                                                                               | MM             | C             | V                        |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

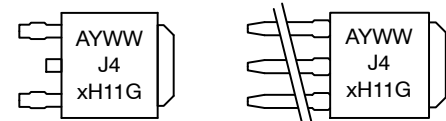
1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

## SILICON POWER TRANSISTORS 8 AMPERES 80 VOLTS, 20 WATTS

#### COMPLEMENTARY



#### MARKING DIAGRAMS



**DPAK**  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 J4xH11 = Device Code  
 x = 4 or 5  
 G = Pb–Free Package

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

# MJD44H11 (NPN), MJD45H11 (PNP)

## THERMAL CHARACTERISTICS

| Characteristic                                   | Symbol          | Max  | Unit                 |
|--------------------------------------------------|-----------------|------|----------------------|
| Thermal Resistance, Junction-to-Case             | $R_{\theta JC}$ | 6.25 | $^{\circ}\text{C/W}$ |
| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 71.4 | $^{\circ}\text{C/W}$ |
| Lead Temperature for Soldering                   | $T_L$           | 260  | $^{\circ}\text{C}$   |

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

## ELECTRICAL CHARACTERISTICS

( $T_A = 25^{\circ}\text{C}$ , common for NPN and PNP, minus sign, “-”, for PNP omitted, unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                                                 |               |    |   |     |               |
|---------------------------------------------------------------------------------|---------------|----|---|-----|---------------|
| Collector-Emitter Sustaining Voltage<br>( $I_C = 30\text{ mA}$ , $I_B = 0$ )    | $V_{CE(sus)}$ | 80 | - | -   | Vdc           |
| Collector Cutoff Current<br>( $V_{CE} = \text{Rated } V_{CEO}$ , $V_{BE} = 0$ ) | $I_{CES}$     | -  | - | 1.0 | $\mu\text{A}$ |
| Emitter Cutoff Current<br>( $V_{EB} = 5\text{ Vdc}$ )                           | $I_{EBO}$     | -  | - | 1.0 | $\mu\text{A}$ |

### ON CHARACTERISTICS

|                                                                                                                             |               |          |        |        |     |
|-----------------------------------------------------------------------------------------------------------------------------|---------------|----------|--------|--------|-----|
| Collector-Emitter Saturation Voltage<br>( $I_C = 8\text{ Adc}$ , $I_B = 0.4\text{ Adc}$ )                                   | $V_{CE(sat)}$ | -        | -      | 1      | Vdc |
| Base-Emitter Saturation Voltage<br>( $I_C = 8\text{ Adc}$ , $I_B = 0.8\text{ Adc}$ )                                        | $V_{BE(sat)}$ | -        | -      | 1.5    | Vdc |
| DC Current Gain<br>( $V_{CE} = 1\text{ Vdc}$ , $I_C = 2\text{ Adc}$ )<br>( $V_{CE} = 1\text{ Vdc}$ , $I_C = 4\text{ Adc}$ ) | $h_{FE}$      | 60<br>40 | -<br>- | -<br>- | -   |

### DYNAMIC CHARACTERISTICS

|                                                                                                                               |          |        |           |        |     |
|-------------------------------------------------------------------------------------------------------------------------------|----------|--------|-----------|--------|-----|
| Collector Capacitance<br>( $V_{CB} = 10\text{ Vdc}$ , $f_{\text{test}} = 1\text{ Mhz}$ )<br>MJD44H11<br>MJD45H11              | $C_{cb}$ | -<br>- | 45<br>130 | -<br>- | pF  |
| Gain Bandwidth Product<br>( $I_C = 0.5\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 20\text{ Mhz}$ )<br>MJD44H11<br>MJD45H11 | $f_T$    | -<br>- | 85<br>90  | -<br>- | MHz |

### SWITCHING TIMES

|                                                                                                       |             |        |            |        |    |
|-------------------------------------------------------------------------------------------------------|-------------|--------|------------|--------|----|
| Delay and Rise Times<br>( $I_C = 5\text{ Adc}$ , $I_{B1} = 0.5\text{ Adc}$ )<br>MJD44H11<br>MJD45H11  | $t_d + t_r$ | -<br>- | 300<br>135 | -<br>- | ns |
| Storage Time<br>( $I_C = 5\text{ Adc}$ , $I_{B1} = I_{B2} = 0.5\text{ Adc}$ )<br>MJD44H11<br>MJD45H11 | $t_s$       | -<br>- | 500<br>500 | -<br>- | ns |
| Fall Time<br>( $I_C = 5\text{ Adc}$ , $I_{B1} = I_{B2} = 0.5\text{ Adc}$ )<br>MJD44H11<br>MJD45H11    | $t_f$       | -<br>- | 140<br>100 | -<br>- | ns |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## MJD44H11 (NPN), MJD45H11 (PNP)

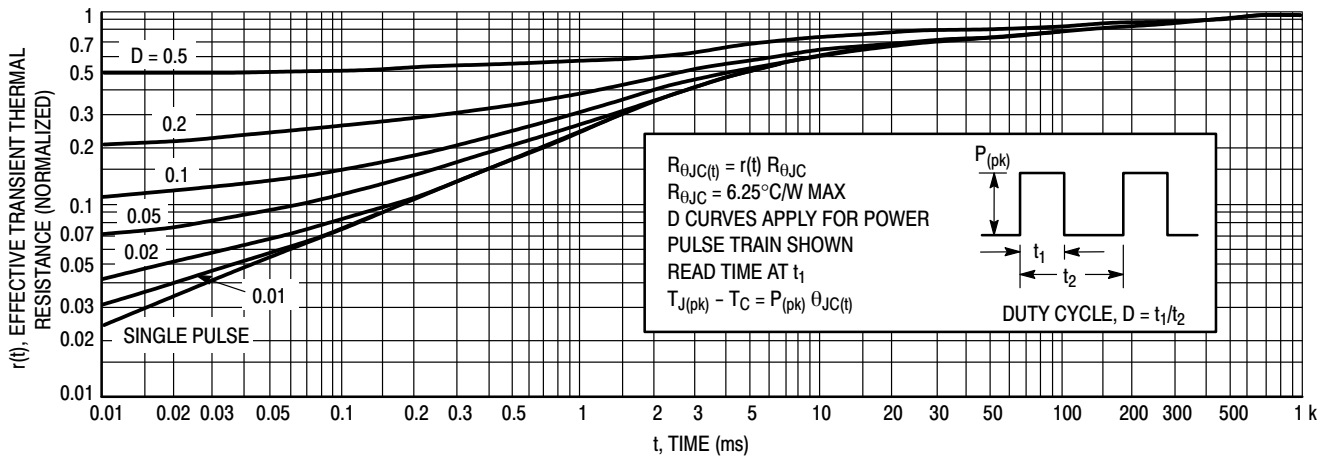


Figure 1. Thermal Response

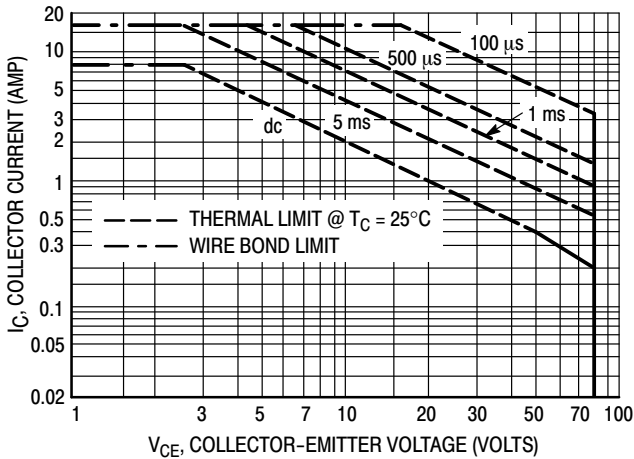


Figure 2. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



Figure 3. Power Derating

## MJD44H11 (NPN), MJD45H11 (PNP)

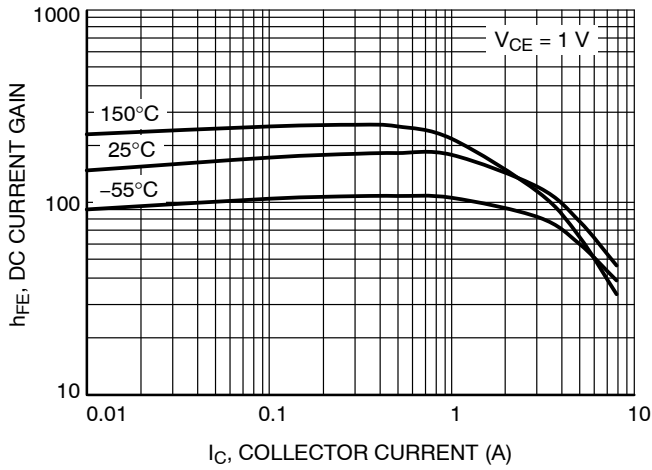


Figure 4. MJD44H11 DC Current Gain

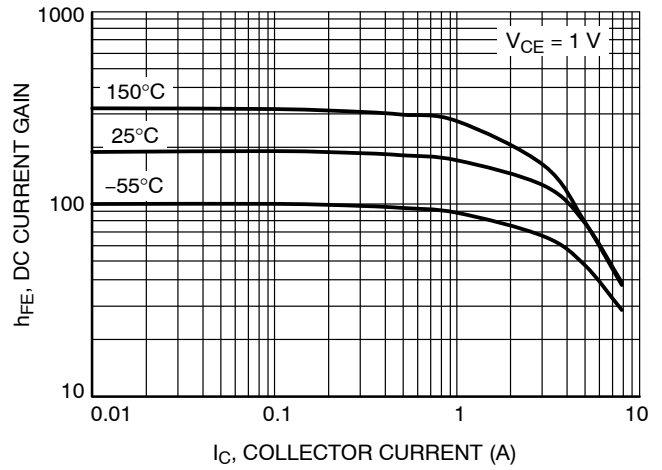


Figure 5. MJD45H11 DC Current Gain

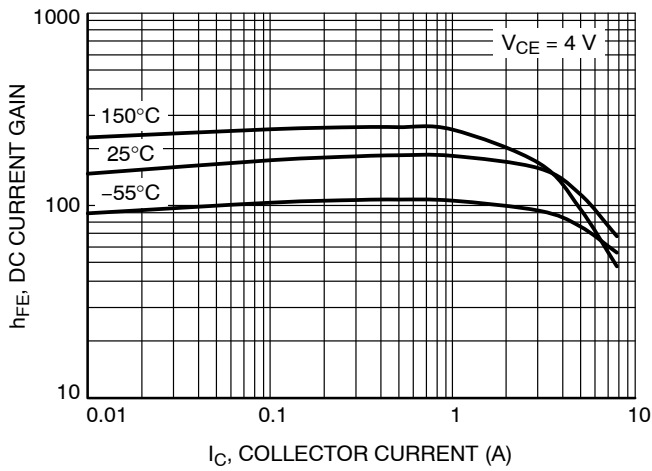


Figure 6. MJD44H11 DC Current Gain

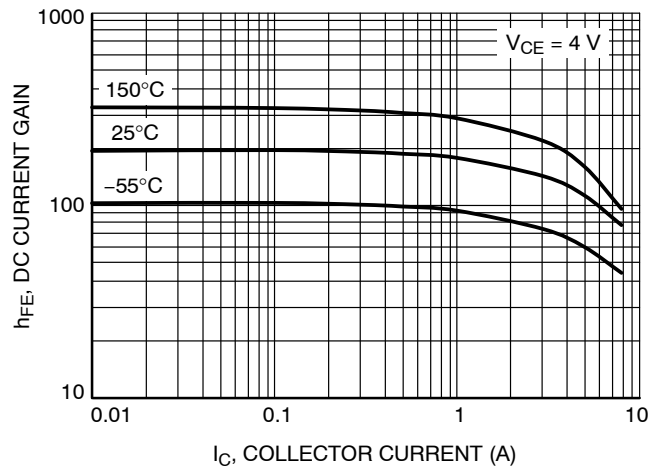


Figure 7. MJD45H11 DC Current Gain

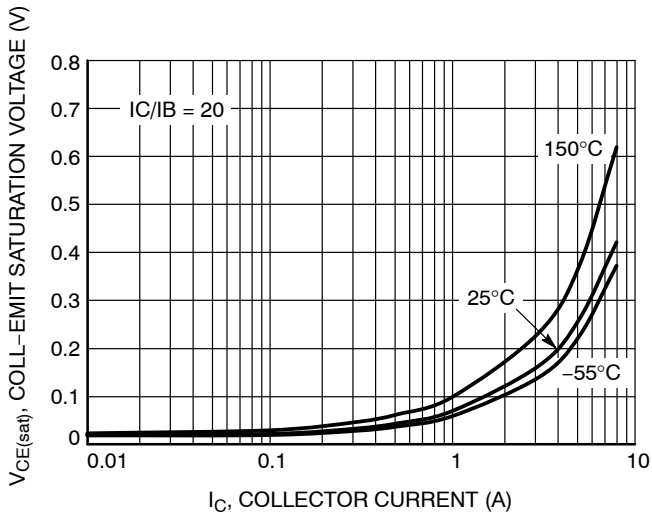


Figure 8. MJD44H11 Saturation Voltage  
 $V_{CE(sat)}$

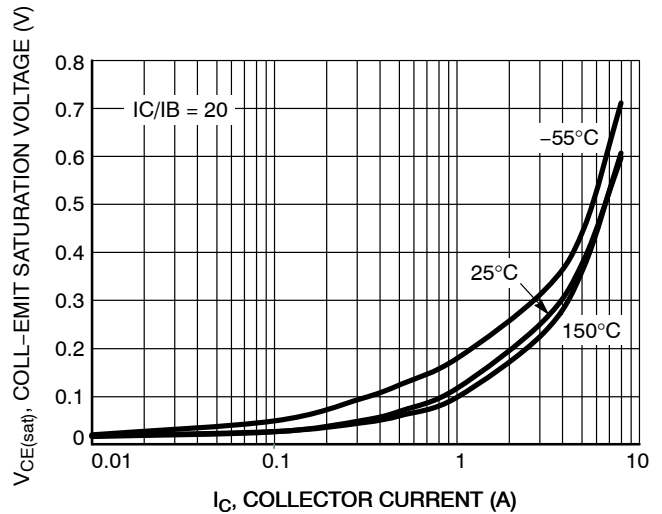


Figure 9. MJD45H11 Saturation Voltage  
 $V_{CE(sat)}$

## MJD44H11 (NPN), MJD45H11 (PNP)



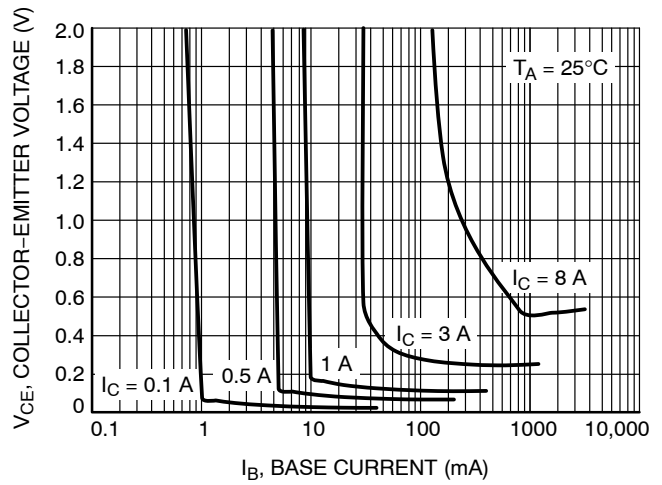
**Figure 10. MJD44H11 Saturation Voltage**  
 $V_{BE(sat)}$



**Figure 11. MJD45H11 Saturation Voltage**  
 $V_{BE(sat)}$



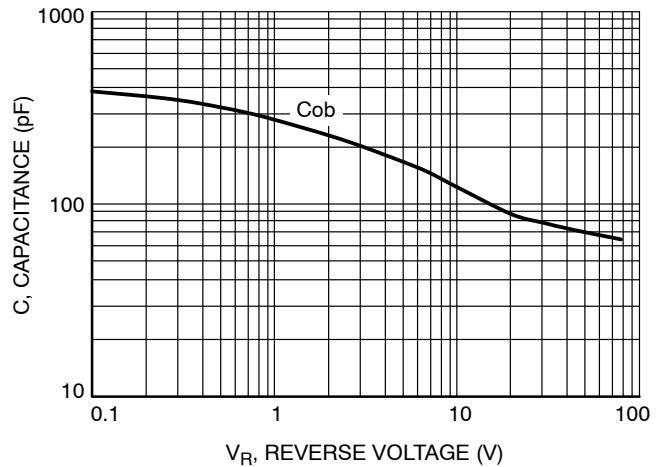
**Figure 12. MJD44H11 Collector Saturation Region**



**Figure 13. MJD45H11 Collector Saturation Region**



**Figure 14. MJD44H11 Capacitance**



**Figure 15. MJD45H11 Capacitance**

## MJD44H11 (NPN), MJD45H11 (PNP)



**Figure 16. MJD44H11**  
Current-Gain-Bandwidth Product



**Figure 17. MJD45H11**  
Current-Gain-Bandwidth Product

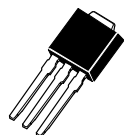
## MJD44H11 (NPN), MJD45H11 (PNP)

### ORDERING INFORMATION

| Device            | Package Type        | Package | Shipping <sup>†</sup> |
|-------------------|---------------------|---------|-----------------------|
| MJD44H11G         | DPAK<br>(Pb-Free)   | 369C    | 75 Units / Rail       |
| NJVMJD44H11G      | DPAK<br>(Pb-Free)   | 369C    | 75 Units / Rail       |
| MJD44H11-1G       | DPAK-3<br>(Pb-Free) | 369D    | 75 Units / Rail       |
| MJD44H11RLG       | DPAK<br>(Pb-Free)   | 369C    | 1,800 / Tape & Reel   |
| NJVMJD44H11RLG*   | DPAK<br>(Pb-Free)   | 369C    | 1,800 / Tape & Reel   |
| MJD44H11T4G       | DPAK<br>(Pb-Free)   | 369C    | 2,500 / Tape & Reel   |
| NJVMJD44H11T4G*   | DPAK<br>(Pb-Free)   | 369C    | 2,500 / Tape & Reel   |
| MJD44H11T5G       | DPAK<br>(Pb-Free)   | 369C    | 2,500 / Tape & Reel   |
| MJD45H11G         | DPAK<br>(Pb-Free)   | 369C    | 75 Units / Rail       |
| NJVMJD45H11G*     | DPAK<br>(Pb-Free)   | 369C    | 75 Units / Rail       |
| MJD45H11-1G       | DPAK-3<br>(Pb-Free) | 369D    | 75 Units / Rail       |
| MJD45H11RLG       | DPAK<br>(Pb-Free)   | 369C    | 1,800 / Tape & Reel   |
| NJVMJD45H11RLG*   | DPAK<br>(Pb-Free)   | 369C    | 1,800 / Tape & Reel   |
| MJD45H11T4G       | DPAK<br>(Pb-Free)   | 369C    | 2,500 / Tape & Reel   |
| NJVMJD45H11T4G*   | DPAK<br>(Pb-Free)   | 369C    | 2,500 / Tape & Reel   |
| NJVMJD44H11D3T4G* | DPAK<br>(Pb-Free)   | 369G    | 2,500 / Tape & Reel   |
| NJVMJD45H11D3T4G* | DPAK<br>(Pb-Free)   | 369G    | 2,500 / Tape & Reel   |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

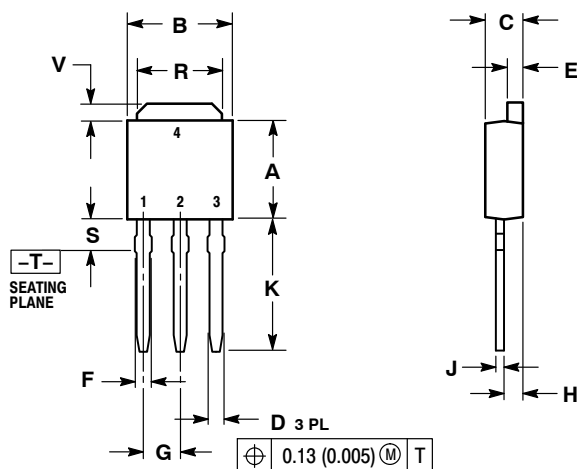
\*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable



DPAK INSERTION MOUNT  
CASE 369  
ISSUE O

DATE 02 JAN 2000

SCALE 1:1



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES    |       | MILLIMETERS |      |
|-----|-----------|-------|-------------|------|
|     | MIN       | MAX   | MIN         | MAX  |
| A   | 0.235     | 0.250 | 5.97        | 6.35 |
| B   | 0.250     | 0.265 | 6.35        | 6.73 |
| C   | 0.086     | 0.094 | 2.19        | 2.38 |
| D   | 0.027     | 0.035 | 0.69        | 0.88 |
| E   | 0.033     | 0.040 | 0.84        | 1.01 |
| F   | 0.037     | 0.047 | 0.94        | 1.19 |
| G   | 0.090 BSC |       | 2.29 BSC    |      |
| H   | 0.034     | 0.040 | 0.87        | 1.01 |
| J   | 0.018     | 0.023 | 0.46        | 0.58 |
| K   | 0.350     | 0.380 | 8.89        | 9.65 |
| R   | 0.175     | 0.215 | 4.45        | 5.46 |
| S   | 0.050     | 0.090 | 1.27        | 2.28 |
| V   | 0.030     | 0.050 | 0.77        | 1.27 |

STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 3:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

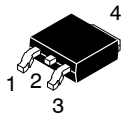
STYLE 4:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 5:  
PIN 1. GATE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 6:  
PIN 1. MT1  
2. MT2  
3. GATE  
4. MT2

|                  |                      |                                                                                                                                                                                     |
|------------------|----------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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| DESCRIPTION:     | DPAK INSERTION MOUNT | PAGE 1 OF 1                                                                                                                                                                         |

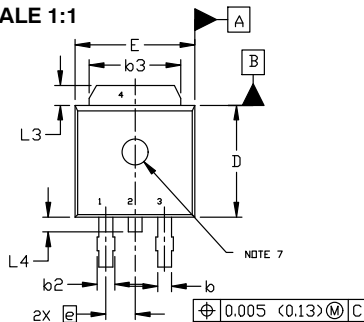
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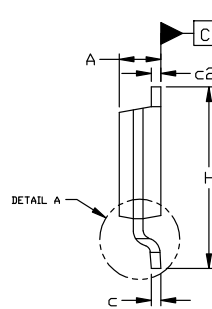
DPAK (SINGLE GAUGE)  
CASE 369C  
ISSUE G

DATE 31 MAY 2023

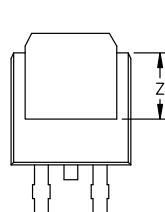
SCALE 1:1



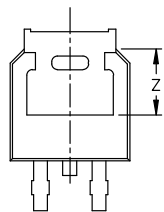
TOP VIEW



SIDE VIEW

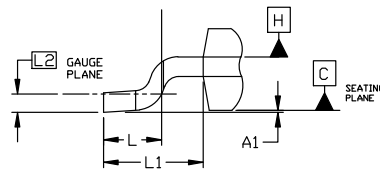
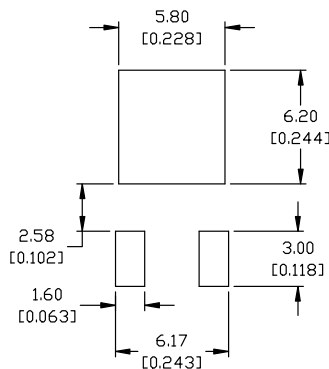


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE  
CONSTRUCTIONS



DETAIL A  
ROTATED 90° CW

NOTES:

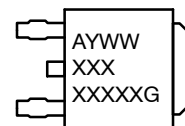
1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN.   | MAX.  | MIN.        | MAX.  |
| A   | 0.086  | 0.094 | 2.18        | 2.38  |
| A1  | 0.000  | 0.005 | 0.00        | 0.13  |
| b   | 0.025  | 0.035 | 0.63        | 0.89  |
| b2  | 0.028  | 0.045 | 0.72        | 1.14  |
| b3  | 0.180  | 0.215 | 4.57        | 5.46  |
| c   | 0.018  | 0.024 | 0.46        | 0.61  |
| c2  | 0.018  | 0.024 | 0.46        | 0.61  |
| D   | 0.235  | 0.245 | 5.97        | 6.22  |
| E   | 0.250  | 0.265 | 6.35        | 6.73  |
| e   | 0.090  | BSC   | 2.29        | BSC   |
| H   | 0.370  | 0.410 | 9.40        | 10.41 |
| L   | 0.055  | 0.070 | 1.40        | 1.78  |
| L1  | 0.114  | REF   | 2.90        | REF   |
| L2  | 0.020  | BSC   | 0.51        | BSC   |
| L3  | 0.035  | 0.050 | 0.89        | 1.27  |
| L4  | ----   | 0.040 | ---         | 1.01  |
| Z   | 0.155  | ----  | 3.93        | ---   |

GENERIC  
MARKING DIAGRAM\*



IC



Discrete

XXXXXX = Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT\*

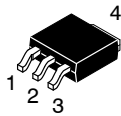
\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

|                                                                       |                                                                       |                                                                  |                                                                            |                                                                   |
|-----------------------------------------------------------------------|-----------------------------------------------------------------------|------------------------------------------------------------------|----------------------------------------------------------------------------|-------------------------------------------------------------------|
| STYLE 1:<br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | STYLE 2:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN          | STYLE 3:<br>PIN 1. ANODE<br>2. CATHODE<br>3. ANODE<br>4. CATHODE | STYLE 4:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE<br>4. ANODE              | STYLE 5:<br>PIN 1. GATE<br>2. ANODE<br>3. CATHODE<br>4. ANODE     |
| STYLE 6:<br>PIN 1. MT1<br>2. MT2<br>3. GATE<br>4. MT2                 | STYLE 7:<br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | STYLE 8:<br>PIN 1. N/C<br>2. CATHODE<br>3. ANODE<br>4. CATHODE   | STYLE 9:<br>PIN 1. ANODE<br>2. CATHODE<br>3. RESISTOR ADJUST<br>4. CATHODE | STYLE 10:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE<br>4. ANODE |

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

|                  |                     |                                                                                                                                                                                  |
|------------------|---------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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| DESCRIPTION:     | DPAK (SINGLE GAUGE) | PAGE 1 OF 1                                                                                                                                                                      |

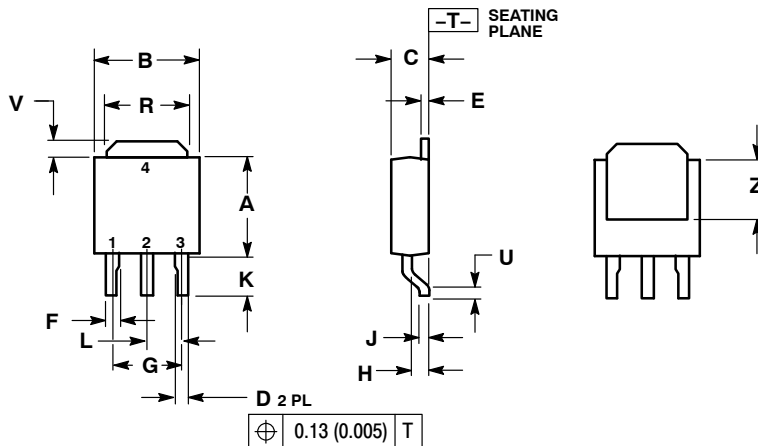
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SCALE 1:1

DPAK-3, SURFACE MOUNT  
CASE 369G  
ISSUE O

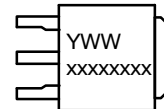
DATE 23 DEC 2003



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES |       | MILLIMETERS |      |
|-----|--------|-------|-------------|------|
|     | MIN    | MAX   | MIN         | MAX  |
| A   | 0.235  | 0.245 | 5.97        | 6.22 |
| B   | 0.250  | 0.265 | 6.35        | 6.73 |
| C   | 0.086  | 0.094 | 2.19        | 2.38 |
| D   | 0.027  | 0.035 | 0.69        | 0.88 |
| E   | 0.018  | 0.023 | 0.46        | 0.58 |
| F   | 0.037  | 0.045 | 0.94        | 1.14 |
| G   | 0.180  | BSC   | 4.58        | BSC  |
| H   | 0.034  | 0.040 | 0.87        | 1.01 |
| J   | 0.018  | 0.023 | 0.46        | 0.58 |
| K   | 0.102  | 0.114 | 2.60        | 2.89 |
| L   | 0.090  | BSC   | 2.29        | BSC  |
| R   | 0.180  | 0.215 | 4.57        | 5.45 |
| U   | 0.020  | ---   | 0.51        | ---  |
| V   | 0.035  | 0.050 | 0.89        | 1.27 |
| Z   | 0.155  | ---   | 3.93        | ---  |

GENERIC  
MARKING DIAGRAM\*



xxxxxxx = Device Code  
Y = Year  
WW = Work Week

- STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR
- STYLE 2:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN
- STYLE 3:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE
- STYLE 4:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE
- STYLE 5:  
PIN 1. GATE  
2. ANODE  
3. CATHODE  
4. ANODE
- STYLE 6:  
PIN 1. MT1  
2. MT2  
3. GATE  
4. MT2
- STYLE 7:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

\*This information is generic. Please refer to device data sheet for actual part marking.

|                  |                       |                                                                                                                                                                                  |
|------------------|-----------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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| DESCRIPTION:     | DPAK-3, SURFACE MOUNT | PAGE 1 OF 1                                                                                                                                                                      |

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